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APPLICANT(s): Ooi et al.

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TITLE: QUANTUM WELL INTERMIXING

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Commissioner of Patents
Washington, D.C. 20231

AMENDMENT

Sir:

This is in response to the Office Action mailed September 24, 2002 (Paper No. 8) in regard to the above-identified patent application. Reconsideration of the rejection of the claims is respectfully solicited in light of the following remarks.

REMARKS

The present invention relates to a novel and inventive method of introducing point defects in a compound semiconductor structure. The structure is irradiated by a source of photons whose energy is at least that of the displacement energy (E_D) of one species within the compound semiconductor. Typically, the structure itself is heated to temperatures of the order of 100 °C (see Figure 5 and first paragraph, page 16) during this process.